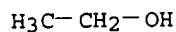


L15 ANSWER 9 OF 12 HCAPLUS COPYRIGHT 2003 ACS on STN
 AN 1999:796011 HCAPLUS
 DN 132:43780
 TI Formation of dielectric layers
 IN Narwankar, Pravin K.; Sahin, Turgut; Urdahl, Randall S.; Velaga, Ankineedu; Liu, Patricia
 PA Applied Materials, Inc., USA
 SO PCT Int. Appl., 41 pp.
 CODEN: PIXXD2
 DT Patent
 LA English
 IC ICM C23C016-56
 ICS C23C016-40; H01L021-3105
 CC 76-10 (Electric Phenomena)
 Section cross-reference(s): 75
 FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
WO 9964645	A1	19991216	WO 1999-US13300	19990611
W: JP, KR				
RW: AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE				
US 2002009861	A1	20020124	US 1998-96858	19980612
EP 1093532	A1	20010425	EP 1999-930223	19990611
R: BE, DE, GB, NL, IE				
JP 2002517914	T2	20020618	JP 2000-553633	19990611
PRAI US 1998-96858	A	19980612		
WO 1999-US13300	W	19990611		

AB An active at. species is generated in a 1st chamber. A dielec. layer formed on a substrate is then exposed to the active at. species in a 2nd chamber sep. from the 1st chamber.
 IT 6074-84-6, Pentaethoxytantalum 172901-22-3
 RL: NUU (Other use, unclassified); PEP (Physical, engineering or chemical process); PROC (Process); USES (Uses)
 (in formation of dielec. layers)
 RN 6074-84-6 HCAPLUS
 CN Ethanol, tantalum(5+) salt (9CI) (CA INDEX NAME)



1/5 Ta(V)

RN 172901-22-3 HCAPLUS
 CN Tantalum, [2-(dimethylamino-.kappa.N)ethanolato-.kappa.O]tetraethoxy-, (OC-6-23)- (9CI) (CA INDEX NAME)

